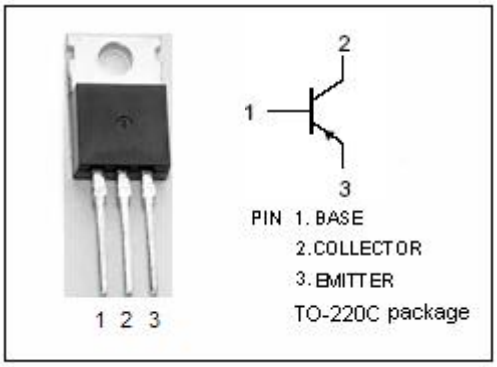
isc Silicon PNP Power Transistor 2SA1129

DESCRIPTION

- Low Collector Saturation Voltage
  :$V_{CE(sat)}$= -0.3(V)(Max)@I_C= -3A
- Large Current Capability-I_C= -7A
- Complement to Type 2SC2654
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

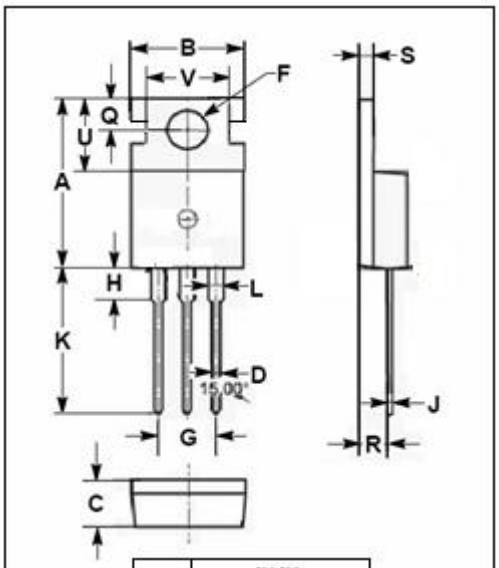


APPLICATIONS

- Designed for mid-switching applications, and is ideal for use as a ramp driver.

ABSOLUTE MAXIMUM RATINGS(T_a=25℃)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	-30	V
V_{CEO}	Collector-Emitter Voltage	-30	V
V_{EBO}	Emitter-Base Voltage	-7	V
I_C	Collector Current-Continuous	-7	A
I_{CM}	Collector Current-Peak	-15	A
I_B	Base Current-Continuous	-3.5	A
P_C	Total Power Dissipation @ T_a=25℃	1.5	W
	Total Power Dissipation @ T_C=25℃	40	
T_J	Junction Temperature	150	℃
T_{stg}	Storage Temperature Range	-55~150	℃



DIM	mm MIN	MAX
A	15.50	15.90
B	9.80	10.20
C	4.20	4.50
D	0.70	0.90
F	3.40	3.70
G	4.98	5.18
H	2.68	2.90
J	0.44	0.60
K	12.80	13.40
L	1.20	1.45
Q	2.70	2.90
R	2.30	2.70
S	1.29	1.35
U	6.45	6.65
V	8.66	8.86

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ELECTRICAL CHARACTERISTICS

T_C=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{CE(sat)-1}$	Collector-Emitter Saturation Voltage	I_C= -3A; I_B= -0.1A			-0.3	V
$V_{CE(sat)-2}$	Collector-Emitter Saturation Voltage	I_C= -5A; I_B= -0.5A			-0.6	V
$V_{BE(sat)-1}$	Base-Emitter Saturation Voltage	I_C= -3A; I_B= -0.1A			-1.5	V
$V_{BE(sat)-2}$	Base-Emitter Saturation Voltage	I_C= -5A; I_B= -0.5A			-2.0	V
I_{CBO}	Collector Cutoff Current	V_{CB}= -30V; I_E= 0			-10	μA
I_{EBO}	Emitter Cutoff Current	V_{EB}= -5V; I_C= 0			-10	μA
h_{FE-1}	DC Current Gain	I_C= -3A ; V_{CE}= -1V	40		200	
h_{FE-2}	DC Current Gain	I_C= -5A ; V_{CE}= -1V	20			

◆ **h_{FE-1} Classifications**

M	L	K
40-80	60-120	100-200